

Product / Process Change Notification



N° 2021-022-A

Dear Customer,

Please find attached our INFINEON Technologies PCN:

Introduction of an additional wafer production location at Infineon Technologies Austria AG, Villach, Austria and introduction of an additional assembly and final test location at Huayi Microelectronics Co., Ltd (HYME), for package TO220 for CoolMOS™ P7 600V and 700V products

Important information for your attention:

- Please respond to this PCN by indicating your decision on the approval form, sign it and return to your sales partner before **21. April 2021**.
- Infineon aligns with the widely-recognized JEDEC STANDARD “**JESD46**“, which stipulates:
“**Lack of acknowledgement of the PCN within 30 days constitutes acceptance of the change.**”

Your prompt reply will help Infineon Technologies to assure a smooth and well executed transition. If Infineon does not hear from your side by the due date, we will assume your full acceptance to this proposed change and its implementation.

Your attention and response to this matter is greatly appreciated.

Infineon Technologies AG
Postal Address Headquarters: Am Campeon 1-15, D-85579 Neubiberg, Phone +49 (0)89 234-0
Chairman of the Supervisory Board: Dr. Wolfgang Eder
Management Board: Dr. Reinhard Ploss (CEO), Dr. Helmut Gassel, Jochen Hanebeck, Dr. Sven Schneider
Registered Office: Neubiberg
Commercial Register: München HRB 126492

Product / Process Change Notification



N° 2021-022-A

► **Products affected:** Please refer to attached affected product list 1_cip21022_a

► **Detailed Change Information:**

Subject: Introduction of an additional wafer production location at Infineon Technologies Austria AG, Villach, Austria and introduction of an additional assembly and final test location at Huayi Microelectronics Co., Ltd (HYME), for package TO220 for CoolMOS™ P7 600V and 700V products

Reason: Introduction of additional wafer production location at Infineon Technologies Austria AG, Villach, Austria and additional as additional assembly and final test location at Huayi Microelectronics Co., Ltd (HYME), for package TO220 as additional capacity to ensure continuity of supply and enable flexible manufacturing

Description:	Old		New	
Wafer Production Location	■ Infineon Technologies Dresden GmbH & Co. KG		■ Infineon Technologies Dresden GmbH & Co. KG	
			Or	
TO220 Assembly and Test Location	■ ASE (Weihai) Inc., China		■ Infineon Technologies Austria AG	
	Or			
	■ Infineon Technologies (Malaysia) Sdn. Bhd		■ ASE (Weihai) Inc., China	
			Or	
			■ Infineon Technologies (Malaysia) Sdn. Bhd	
			Or	
			■ Huayi Microelectronics Co., Ltd (HYME) in Xi'an,	

► **Product Identification:** Traceability via Baunumber, Lotnumber

External traceability: Product Barcode Label

► **Impact of Change:** **NO** change on electrical and thermal performance
NO impact on the device reliability as proven via product qualification.
NO impact on the electrical parameters and device processability at customer end.

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- The package outer dimensions remain unchanged

► Attachments:

Affected product list : 1_cip21022_a
Qualification Test Report : 2_cip21022_a
Customer Info Package : 3_cip21022_a

► Time Schedule:

- | | |
|-------------------------------|---|
| ■ Final qualification report: | available |
| ■ First samples available: | on request |
| ■ Intended start of delivery: | 01-September-2021 or earlier upon customer approval |

If you have any questions, please do not hesitate to contact your local Sales office.



PCN N° 2021-022-A

25.02.2021

Introduction of an additional wafer production location at Infineon Technologies Austria AG, Villach, Austria and introduction of an additional assembly and final test location at Huayi Microelectronics Co., Ltd (HYME), for package TO220 for CoolMOS™ P7 600V and 700V products

Reason for choosing the following test vehicles:

IPAN60R280P7S
IPN60R360P7S
IPD60R180P7S
IPSA70R900P7S

P7 600V technology in TO220FP narrow lead, medium chip of family qualification ; THD

P7 600V technology in SOT223, medium chip of family qualification; SMD

P7 600V technology in TO252, smallest chip of family qualification; SMD

P7 600V technology in TO220FP wide creepage, biggest chip of family qualification; THD

Scope of qualification: All CoolMOS™ P7S 600V products produced at Infineon Technologies Villach; Austria

Assessment of Q-Results: pass standard grade

Stress test	Abbreviation	Test conditions	Readout	IPAN60R280P7S	IPN60R360P7S	IPD60R180P7S	IPAW60R180P7S
IFX Package type				PG-TO220FP nl	PG-SOT223	PG-TO252	PG-TO220FPW
Assembly line location				TFME	ASE	HYME	HYME
				fails / stressed	fails / stressed	fails / stressed	fails / stressed
MSL Preconditioning J-STD020 / JESD22 A113	PC	MSL and 3 x reflow at 260°C		n.a.	MSL1, 260°C	MSL3, 260°C	n.a.
Temperature Cycling JESD22-A104	TC*	-55°C - +150°C	0c precon 500c 1000c	0 / 77 - 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 -	0 / 77 - 0 / 77 -
Unbiased Temperature/Humidity JESD22-A118	UHAST*	Ta = 130°C, RH = 85%	0h precon 96 h	0 / 77 - 0 / 77	0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77	0 / 77 - 0 / 77
High Humidity High Temp. Reverse Bias JESD22-A101	H3TRB*	T = 85°C RH = 85% VDS = 100V	0h precon 168h 500h 1000h	0 / 77 - 0 / 77 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77 -	0 / 77 - 0 / 77 0 / 77 -
High Temperature Reverse Bias JESD22-A108	HTRB*	Ta ≥ 150°C VDS ≥ 80% VDS max	0h precon 168h 500h 1000h	0 / 77 - 0 / 77 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77 -	0 / 77 - 0 / 77 0 / 77 -
High Temperature Gate stress JESD22-A108	HTGS*	Ta = 150°C VGS = ±20V	0h precon 168h 500h 1000h	0 / 77 - 0 / 77 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77 -	0 / 77 - 0 / 77 0 / 77 -
Intermitted Operational Life Test MIL-STD 750/Meth.1037	IOL*	Delta T = 100K n = 7500 cyc	0c precon 7500c 15000c	0 / 77 - 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 -	0 / 77 - 0 / 77 -
Wave solder simulation for SMD devices JESD22-A111	WS	T=260°C / 1 x 10s and Temperature Cycling from -55°C to +150°C	0h WS 100c	n.a	0 / 30 0 / 30 0 / 30	0 / 30 0 / 30 0 / 30	n.a
Resistance to Solder Heat JESD22-B106	RSH	3x Solder dipping @ 270°C, 7s (for Pb free)	0h RSH	0 / 30 0 / 30	covered by precon	covered by precon	0 / 30 0 / 30
Electrical Parameter Assessment JESD86	ED	Ta = -55°C / 25°C / 150°C	-55°C +25°C +150°C	0 / 50 0 / 50 0 / 50	0 / 50 0 / 50 0 / 50	0 / 50 0 / 50 0 / 50	0 / 50 0 / 50 0 / 50

* PC is done only for SMD Packages before UHAST, TC, IOL, HTGS, HTRB and H3TRB stress tests

Abbreviations: - not performed



PCN N° 2021-022-A

25.02.2021

Introduction of an additional wafer production location at Infineon Technologies Austria AG, Villach, Austria and introduction of an additional assembly and final test location at Huayi Microelectronics Co., Ltd (HYME), for package TO220 for CoolMOS™ P7 600V and 700V products

Reason for choosing the following test vehicles:
IPB60R045P7 P7 600V technology in TO263, medium chip of family qualification ; SMD
IPL60R065P7 P7 600V technology in VSON-4, medium chip of family qualification; SMD
IPD60R180P7 P7 600V technology in TO252, medium chip of family qualification; SMD
IPA60R060P7 P7 600V technology in TO220FP, medium chip of family qualification; THD
IPW60R024P7 P7 600V technology in TO247, biggest chip of family qualification; THD
IPD60R600P7 P7 600V technology in TO252, smallest chip of family qualification; SMD
IPP60R060P7 P7 600V technology in TO220, medium chip of family qualification; THD

Scope of qualification: All CoolMOS™ P7 600V products produced at Infineon Technologies Villach; Austria

Assessment of Q-Results: pass industrial grade

Stress test	Abbreviation	Test conditions	Readout	IPB60R045P7	IPL60R065P7	IPD60R180P7	IPA60R060P7	IPW60R024P7	IPD60R600P7	IPP60R060P7
IFX Package type				PG-TO263	PG-VSON-4	PG-TO252	PG-TO220	PG-TO247	PG-TO252	PG-TO220
Assembly line location				MAL	MAL	TFME	TFME	TFME	ASE	ASE
				fails / stressed	fails / stressed	fails / stressed	fails / stressed	fails / stressed	fails / stressed	fails / stressed
MSL Preconditioning J-STD020 / JESD22 A113	PC	MSL and 3 x reflow at 260°C		MSL1, 260°C	MSL2a, 260°C	MSL1, 260°C	n.a.	n.a.	MSL1, 260°C	n.a.
Temperature Cycling JESD22-A104	TC*	-55°C - +150°C VSON-4: -40°C - +150°C	0c	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			precon	0 / 77	0 / 77	0 / 77	-	-	0 / 77	-
			500c	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			1000c	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
Unbiased Temperature/Humidity JESD22-A118	UHASt*	Ta = 130°C, RH = 85%	0h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			precon	0 / 77	0 / 77	0 / 77	-	-	0 / 77	-
			96 h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			0h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
High Humidity High Temp. Reverse Bias JESD22-A101	H3TRB*	T = 85°C RH = 85% VDS = 100V	precon	0 / 77	0 / 77	0 / 77	-	-	0 / 77	-
			168h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			500h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			1000h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
High Temperature Reverse Bias JESD22-A108	HTRB*	Ta ≥ 150°C VDS ≥ 80% VDS max	0h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			precon	0 / 77	0 / 77	0 / 77	-	-	0 / 77	-
			168h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			500h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
High Temperature Gate stress JESD22-A108	HTGS*	Ta = 150°C VGS = ±20V	0h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			precon	0 / 77	0 / 77	0 / 77	-	-	0 / 77	-
			168h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			500h	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
Intermitted Operational Life Test MIL-STD 750/Meth.1037	IOL*	Delta T = 100K n = 15000 cyc	0c	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			precon	0 / 77	0 / 77	0 / 77	-	-	0 / 77	-
			7500c	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
			15000c	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77	0 / 77
Wave solder simulation for SMD devices JESD22-A111	WS	T=260°C / 1 x 10s and Temperature Cycling from -55°C to +150°C VSON-4: -40°C - +150°C	0h	0 / 30	0 / 30	0 / 30	n.a	n.a	0 / 30	n.a
			WS	0 / 30	0 / 30	0 / 30			0 / 30	
			100c	0 / 30	0 / 30	0 / 30			0 / 30	
Resistance to Solder Heat JESD22-B106	RSH	3x Solder dipping @ 270°C, 7s (for Pb free)	0h RSH	covered by precon	covered by precon	covered by precon	0 / 30 0 / 30	0 / 30 0 / 30	covered by precon	0 / 30 0 / 30
Electrical Parameter Assessment JESD86	ED	Ta = -55°C / 25°C / 150°C	-55°C	0 / 50	0 / 50	0 / 50	0 / 50	0 / 50	0 / 50	0 / 50
			+25°C	0 / 50	0 / 50	0 / 50	0 / 50	0 / 50	0 / 50	0 / 50
			+150°C	0 / 50	0 / 50	0 / 50	0 / 50	0 / 50	0 / 50	0 / 50

* PC is done only for SMD Packages before UHASt, TC, IOL, HTGS, HTRB and H3TRB stress tests

Abbreviations: - not performed



PCN N° 2021-022-A

25.02.2021

Introduction of an additional wafer production location at Infineon Technologies Austria AG, Villach, Austria and introduction of an additional assembly and final test location at Huayi Microelectronics Co., Ltd (HYME), for package TO220 for CoolMOS™ P7 600V and 700V products

Reason for choosing the following test vehicles:
IPAN70R360P7S P7 700V technology in TO220FP narrow lead, biggest chip of family qualification ; THD
IPD70R900P7S P7 700V technology in TO252, medium chip of family qualification; SMD
IPN70R2K0P7S P7 700V technology in SOT223, smallest chip of family qualification; SMD
IPSA70R900P7S P7 700V technology in TO251, medium chip of family qualification; THD

Scope of qualification: All CoolMOS™ P7 700V products produced at Infineon Technologies Villach; Austria

Assessment of Q-Results: pass standard grade

Stress test	Abbreviation	Test conditions	Readout	IPAN70R360P7S	IPD70R900P7S	IPN70R2K0P7S	IPSA70R900P7S
IFX Package type				PG-TO220FP nl	PG-TO252	PG-SOT223	PG-TO251
Assembly line location				HYME	HYME	ASE	TFME
				fails / stressed	fails / stressed	fails / stressed	fails / stressed
MSL Preconditioning J-STD020 / JESD22 A113	PC	MSL and 3 x reflow at 260°C		n.a.	MSL3, 260°C	MSL1, 260°C	n.a.
Temperature Cycling JESD22-A104	TC*	-55°C - +150°C	0c precon 500c 1000c	0 / 77 - 0 / 77 -	0 / 77 0 / 77 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 - 0 / 77 -
Unbiased Temperature/Humidity JESD22-A118	UHASt*	Ta = 130°C, RH = 85%	0h precon 96 h	0 / 77 - 0 / 77	0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77	0 / 77 - 0 / 77
High Humidity High Temp. Reverse Bias JESD22-A101	H3TRB*	T = 85°C RH = 85% VDS = 100V	0h precon 168h 500h 1000h	0 / 77 - 0 / 77 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 - 0 / 77 0 / 77 -
High Temperature Reverse Bias JESD22-A108	HTRB*	Ta ≥ 150°C VDS ≥ 80% VDS max	0h precon 168h 500h 1000h	0 / 77 - 0 / 77 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 - 0 / 77 0 / 77 -
High Temperature Gate stress JESD22-A108	HTGS*	Ta = 150°C VGS = ±20V	0h precon 168h 500h 1000h	0 / 77 - 0 / 77 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 - 0 / 77 0 / 77 -
Intermittent Operational Life Test MIL-STD 750/Meth.1037	IOL*	Delta T = 100K n = 7500 cyc	0c precon 7500c 15000c	0 / 77 - 0 / 77 -	0 / 77 0 / 77 0 / 77 -	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 - 0 / 77 -
Wave solder simulation for SMD devices JESD22-A111	WS	T=260°C / 1 x 10s and Temperature Cycling from -55°C to +150°C	0h WS 100c	n.a	0 / 30 0 / 30 0 / 30	0 / 30 0 / 30 0 / 30	n.a
Resistance to Solder Heat JESD22-B106	RSH	3x Solder dipping @ 270°C, 7s (for Pb free)	0h RSH	0 / 30 0 / 30	covered by precon	covered by precon	0 / 30 0 / 30
Electrical Parameter Assessment JESD86	ED	Ta = -55°C / 25°C / 150°C	-55°C +25°C +150°C	0 / 50 0 / 50 0 / 50	0 / 50 0 / 50 0 / 50	0 / 50 0 / 50 0 / 50	0 / 50 0 / 50 0 / 50

* PC is done only for SMD Packages before UHASt, TC, IOL, HTGS, HTRB and H3TRB stress tests
Abbreviations: - not performed

RESTRICTED

Qualification Test Report



Date: 21.01.2021

PCN N° 2021-022-A

Introduction of an additional wafer production location at Infineon Technologies Austria AG, Villach, Austria and introduction of an additional assembly and final test location at Huayi Microelectronics Co., Ltd (HYME), for package TO220 for CoolMOS™ P7 600V and 700V products

Reason for choosing following test vehicle:

IPP90R800C3 C3 Technology in PG-TO220-3; THD
 IPP60R099CP CP Technology in PG-TO220-3; THD
 IPP60R190C6 C6 Technology in PG-TO220-3; THD
 IPP80R1K4P7 P7 Technology in PG-TO220-3; THD
 IPP60R090CFD7 CFD7 Technology in PG-TO220-3; THD

Extension of qualification: All CoolMOS™ products in TO220-3 assembled at HYME

Assessment of Q-Results: PASS industrial grade

Stress test	Abbreviation	Test conditions	Readout	IPP90R800C3	IPP60R099CP	IPP60R190C6	IPP80R1K4P7	IPP60R090CFD7
Temperature Cycling JESD22 A104	TC	-55°C - +150°C	0 c 500 c 1000 c	0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77
Unbiased Highly Accelerated StressTest JESD22 A118	UHASt	130°C / 85% rh	0 h 96 h	0 / 77 0 / 77	0 / 77 0 / 77	0 / 77 0 / 77	0 / 77 0 / 77	0 / 77 0 / 77
High Humidity High Temp. Reverse Bias JESD22 A101	H3TRB	T = 85 °C RH = 85% VDS = 100 V	0 h 168 h 500 h 1000 h	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77
High Temperature Reverse Bias JESD22 A108	HTRB	Ta ≥ 150°C V ≥ 80% VDS max	0 h 168 h 500 h 1000 h	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77
High Temperature Gate stress JESD22 A108	HTGS	Ta = 150 °C VGS = ±20 V	0 h 168 h 500 h 1000 h	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77 0 / 77
Intermittent Operational Life Test MIL-STD 750/Meth.1037	IOL	Delta T = 100 K n = 15000 cyc	0 c 7500 c 15000 c	0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77	0 / 77 0 / 77 0 / 77
Electrical Distribution JESD86	ED	-55 °C +25 °C +150 °C		0 / 50 0 / 50 0 / 50	0 / 50 0 / 50 0 / 50	0 / 50 0 / 50 0 / 50	0 / 50 0 / 50 0 / 50	0 / 50 0 / 50 0 / 50

PCN 2021-022-A

Introduction of an additional wafer production location at Infineon Technologies Austria AG, Villach, Austria and introduction of an additional assembly and final test location at Huayi Microelectronics Co., Ltd (HYME), for package TO220 for CoolMOS™ P7 600V and 700V products



Sales name	SP number	OPN	Package
IPA60R060P7	SP001658404	IPA60R060P7XKSA1	PG-TO220-3
IPA60R080P7	SP001658398	IPA60R080P7XKSA1	PG-TO220-3
IPA60R099P7	SP001658390	IPA60R099P7XKSA1	PG-TO220-3
IPA60R120P7	SP001658376	IPA60R120P7XKSA1	PG-TO220-3
IPA60R120P7 E8191	SP001728984	IPA60R120P7E8191XKSA1	PG-TO220-3
IPA60R160P7	SP001866014	IPA60R160P7XKSA1	PG-TO220-3
IPA60R180P7	SP001606042	IPA60R180P7XKSA1	PG-TO220-3
IPA60R180P7S	SP001606066	IPA60R180P7SXKSA1	PG-TO220-3
IPA60R280P7	SP001658302	IPA60R280P7XKSA1	PG-TO220-3
IPA60R280P7S	SP001658160	IPA60R280P7SXKSA1	PG-TO220-3
IPA60R280P7S E8228	SP002367752	IPA60R280P7SE8228XKSA1	PG-TO220-3
IPA60R360P7	SP001606040	IPA60R360P7XKSA1	PG-TO220-3
IPA60R360P7 E8232	SP004134526	IPA60R360P7E8232XKSA1	PG-TO220-3
IPA60R360P7S	SP001606068	IPA60R360P7SXKSA1	PG-TO220-3
IPA60R360P7S E8228	SP002367774	IPA60R360P7SE8228XKSA1	PG-TO220-3
IPA60R600P7	SP001618084	IPA60R600P7XKSA1	PG-TO220-3
IPA60R600P7S	SP001658294	IPA60R600P7SXKSA1	PG-TO220-3
IPA60R600P7S E8228	SP002367778	IPA60R600P7SE8228XKSA1	PG-TO220-3
IPA70R360P7S	SP001499698	IPA70R360P7SXKSA1	PG-TO220-3
IPA70R450P7S	SP001664868	IPA70R450P7SXKSA1	PG-TO220-3
IPA70R600P7S	SP001499700	IPA70R600P7SXKSA1	PG-TO220-3
IPA70R750P7S	SP001664858	IPA70R750P7SXKSA1	PG-TO220-3
IPA70R900P7S	SP001600942	IPA70R900P7SXKSA1	PG-TO220-3
IPAN60R180P7S	SP002367740	IPAN60R180P7SXKSA1	PG-TO220-3
IPAN60R280P7S	SP001866076	IPAN60R280P7SXKSA1	PG-TO220-3
IPAN60R360P7S	SP001866154	IPAN60R360P7SXKSA1	PG-TO220-3
IPAN60R600P7S	SP001866160	IPAN60R600P7SXKSA1	PG-TO220-3
IPAN70R360P7S	SP001682066	IPAN70R360P7SXKSA1	PG-TO220-3
IPAN70R450P7S	SP001721526	IPAN70R450P7SXKSA1	PG-TO220-3
IPAN70R600P7S	SP001682068	IPAN70R600P7SXKSA1	PG-TO220-3
IPAN70R750P7S	SP001721536	IPAN70R750P7SXKSA1	PG-TO220-3
IPAN70R900P7S	SP001703476	IPAN70R900P7SXKSA1	PG-TO220-3
IPAW60R180P7S	SP001606072	IPAW60R180P7SXKSA1	PG-TO220-3
IPAW60R280P7S	SP001658180	IPAW60R280P7SXKSA1	PG-TO220-3
IPAW60R280P7S E8228	SP002367782	IPAW60R280P7SE8228XKSA1	PG-TO220-3
IPAW60R360P7S	SP001606074	IPAW60R360P7SXKSA1	PG-TO220-3
IPAW60R360P7S E8228	SP002367786	IPAW60R360P7SE8228XKSA1	PG-TO220-3
IPAW60R600P7S	SP001618082	IPAW60R600P7SXKSA1	PG-TO220-3
IPAW60R600P7S E8228	SP002367792	IPAW60R600P7SE8228XKSA1	PG-TO220-3
IPB60R045P7	SP001866168	IPB60R045P7ATMA1	PG-TO263-3
IPB60R060P7	SP001664882	IPB60R060P7ATMA1	PG-TO263-3
IPB60R080P7	SP001664898	IPB60R080P7ATMA1	PG-TO263-3
IPB60R099P7	SP001664910	IPB60R099P7ATMA1	PG-TO263-3
IPB60R120P7	SP001664922	IPB60R120P7ATMA1	PG-TO263-3
IPB60R180P7	SP001664934	IPB60R180P7ATMA1	PG-TO263-3
IPB60R280P7	SP001664942	IPB60R280P7ATMA1	PG-TO263-3
IPB60R360P7	SP001664948	IPB60R360P7ATMA1	PG-TO263-3
IPC60R024P7	SP001878406	IPC60R024P7X7SA1	N.A.
IPC60R037P7	SP001681328	IPC60R037P7X7SA1	N.A.
IPC60R045P7	SP001878408	IPC60R045P7X7SA1	N.A.
IPC60R060P7	SP001681330	IPC60R060P7X7SA1	N.A.
IPC60R080P7	SP001681332	IPC60R080P7X7SA1	N.A.
IPC60R099P7	SP001681334	IPC60R099P7X7SA1	N.A.
IPC60R120P7	SP001681336	IPC60R120P7X7SA1	N.A.
IPC60R160P7	SP001878410	IPC60R160P7X7SA1	N.A.
IPC60R180P7	SP001681338	IPC60R180P7X7SA1	N.A.
IPC60R280P7	SP001681340	IPC60R280P7X7SA1	N.A.
IPC60R360P7	SP001681342	IPC60R360P7X7SA1	N.A.
IPC60R600P7	SP001681344	IPC60R600P7X7SA1	N.A.
IPC70R1K2P7	SP001664758	IPC70R1K2P7X7SA1	N.A.
IPC70R1K4P7	SP001643672	IPC70R1K4P7X7SA1	N.A.
IPC70R2K0P7	SP001664756	IPC70R2K0P7X7SA1	N.A.
IPC70R360P7	SP001643674	IPC70R360P7X7SA1	N.A.
IPC70R450P7	SP001664762	IPC70R450P7X7SA1	N.A.
IPC70R600P7	SP001643676	IPC70R600P7X7SA1	N.A.
IPC70R750P7	SP001664760	IPC70R750P7X7SA1	N.A.
IPC70R900P7	SP001643678	IPC70R900P7X7SA1	N.A.
IPD60R180P7	SP001606052	IPD60R180P7ATMA1	PG-TO252-3

PCN 2021-022-A

Introduction of an additional wafer production location at Infineon Technologies Austria AG, Villach, Austria and introduction of an additional assembly and final test location at Huayi Microelectronics Co., Ltd (HYME), for package TO220 for CoolMOS™ P7 600V and 700V products



Sales name	SP number	OPN	Package
IPD60R180P7S	SP001658138	IPD60R180P7SAUMA1	PG-TO252-3
IPD60R180P7S E8228	SP002367798	IPD60R180P7SE8228AUMA1	PG-TO252-3
IPD60R280P7	SP001658316	IPD60R280P7ATMA1	PG-TO252-3

PCN-2021-022-A

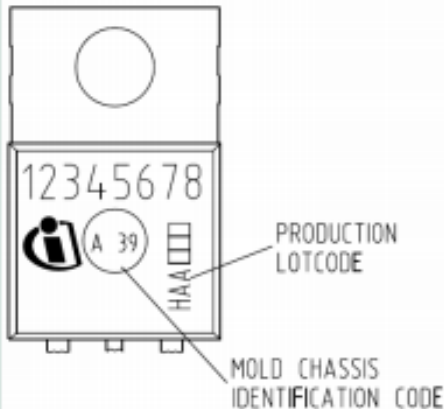
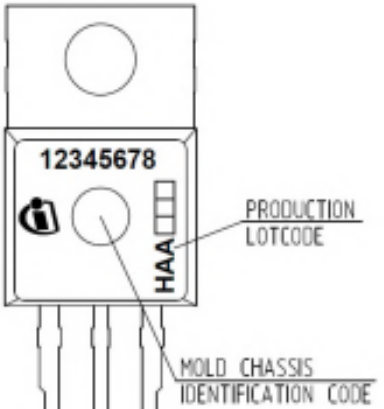
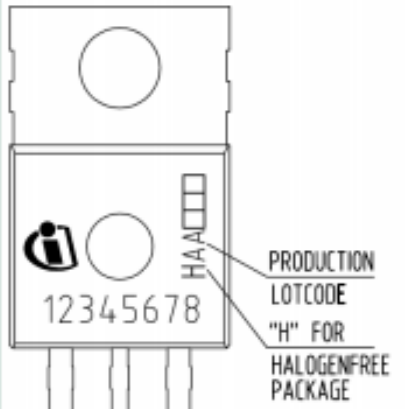
Introduction of an additional wafer production location at Infineon Technologies Austria AG, Villach, Austria and introduction of an additional assembly and final test location at Huayi Microelectronics Co., Ltd (HYME), for package TO220 for CoolMOS™ P7 600V and 700V products

2021-03-05

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Marking Pattern

MAL TO220-3	ASE-WH TO220-3	HYME TO220-3
 The diagram shows the marking pattern for the MAL TO220-3 package. It features a circular window at the top. Below it, the numbers 12345678 are printed. To the left of the numbers is the Infineon logo. To the right of the numbers is a circle containing 'A 39'. Below the circle is the text 'HAA' with three small squares to its right. A line points from the text 'PRODUCTION LOTCODE' to the 'HAA' area. Another line points from the text 'MOLD CHASSIS IDENTIFICATION CODE' to the 'A 39' circle.	 The diagram shows the marking pattern for the ASE-WH TO220-3 package. It features a circular window at the top. Below it, the numbers 12345678 are printed. To the left of the numbers is the Infineon logo. To the right of the numbers is a circle. Below the circle is the text 'HAA' with three small squares to its right. A line points from the text 'PRODUCTION LOTCODE' to the 'HAA' area. Another line points from the text 'MOLD CHASSIS IDENTIFICATION CODE' to the circle.	 The diagram shows the marking pattern for the HYME TO220-3 package. It features a circular window at the top. Below it, the numbers 12345678 are printed. To the left of the numbers is the Infineon logo. To the right of the numbers is a circle. Below the circle is the text 'HAA' with three small squares to its right. A line points from the text 'PRODUCTION LOTCODE' to the 'HAA' area. Another line points from the text '"H" FOR HALOGENFREE PACKAGE' to the 'H' in 'HAA'.



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